HFZT

1N4001-------1N4007

PLASTIC SILICON RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V CURRENT: 1.0 A

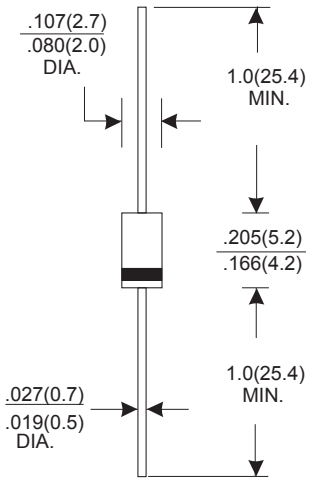
FEATURES

- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability
- Epoxy:UL 94V-0 rate flame retardant

MECHANICAL DATA

- Case style: DO-41plastic molded
- Terminals: Lead solderable per MIL-STD-750,method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any

DO-41



Dimensions in inches and(millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

TYPE NUMBER		1N4001	1N4002	1N4003	1N4004	1N4005	1N4006	1N4007	UNITS
Maximun Recurrent Peak Reverse Voltage		50	100	200	400	600	800	1000	V
Maximum RMS Voltage		35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		50	100	200	400	600	800	1000	V
Maximum average forw ard rectified Current9.5mm lead length,@T_A=75℃		1.0							A
Peak Forward Surge Current,8.3 ms single half sine-wave superimposed on rated load (JEDEC method)		30							A
Maximum Instantaneous Forward Voltage at 1.0A		1.0							V
Maximum DC Reverse Current	Ta=25℃	5.0							μA
at Rated DC Blocking Voltage	Ta=100℃	50							μA
Typical Junction Capacitance(Note 1)		15							Pf
Typical Thermal Resistance RθJA(Note 2)		50							℃/W
Operating and Storage Temperature RangeTJ,Tstg		-65--+125							℃

1.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2.Thermal Resistance from Junction to Ambient.375"(9.5mm) lead length.

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RATINGS AND CHARACTERISTIC CURVES

FIG.1-TYPICAL FORWARD CHARACTERISTICS

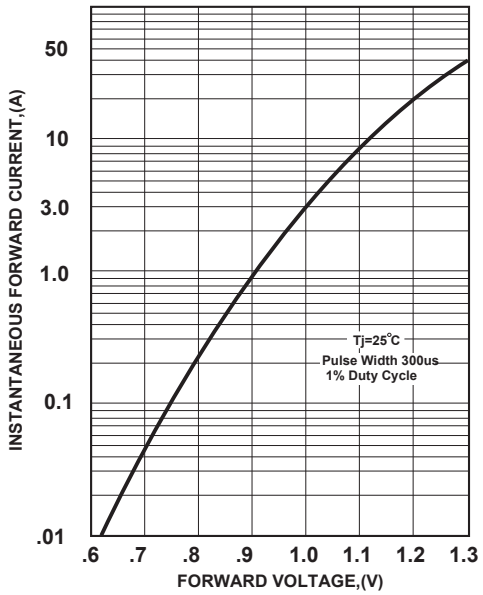

FIG.2 -- PULSE DERATING CURVE

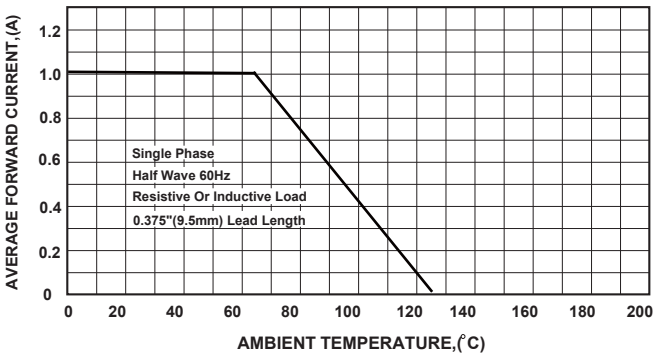

FIG.3 - TYPICAL REVERSE CHARACTERISTICS

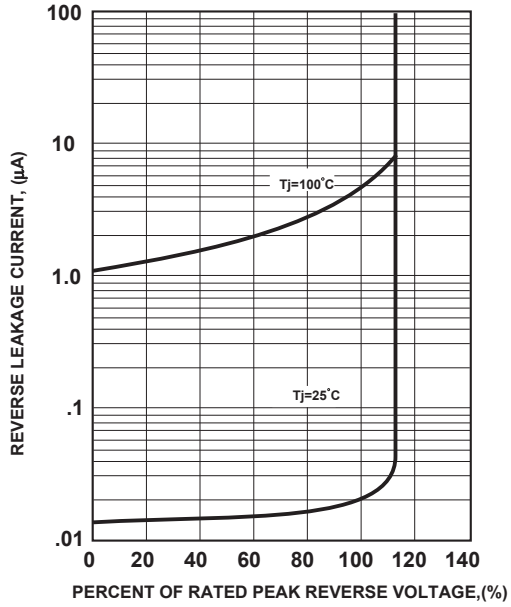

FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

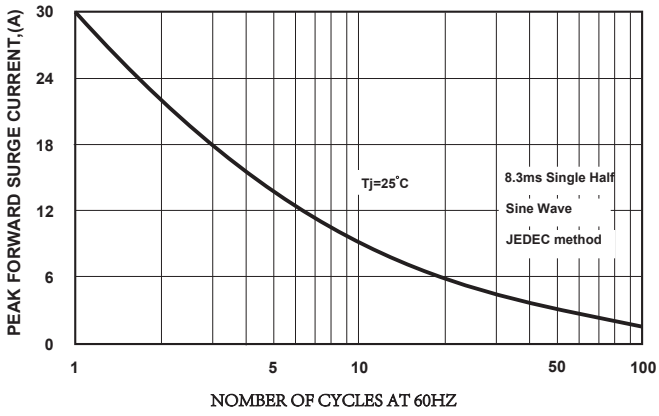

FIG.5-TYPICAL JUNCTION CAPACITANCE